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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I <sup>2</sup> C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I2S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l051r8t7

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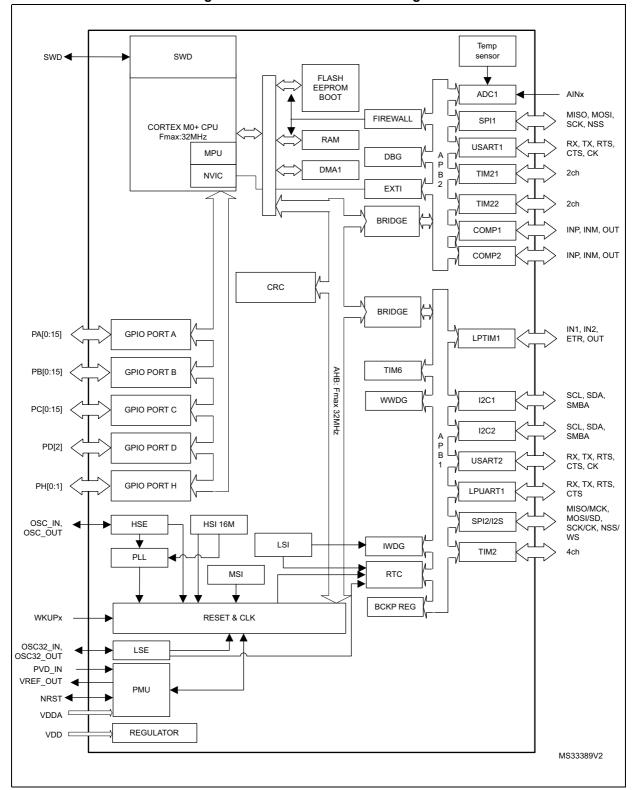


Figure 1. STM32L051x6/8 block diagram



Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)<sup>(1)</sup>

			Low-	Low-		Stop	5	Standby
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
High Speed External (HSE)	0	0	0	0				
Low Speed Internal (LSI)	0	0	0	0	0		0	
Low Speed External (LSE)	0	0	0	0	0		0	
Multi-Speed Internal (MSI)	0	0	Υ	Y				
Inter-Connect Controller	Y	Y	Y	Y	Υ			
RTC	0	0	0	0	0	0	0	
RTC Tamper	0	0	0	0	0	0	0	0
Auto WakeUp (AWU)	0	0	0	0	0	0	0	0
USART	0	0	0	0	O <sup>(3)</sup>	0	-	
LPUART	0	0	0	0	O <sup>(3)</sup>	0	-	
SPI	0	0	0	0				
I2C	0	0	0	0	O <sup>(4)</sup>	0		
ADC	0	0						
Temperature sensor	0	0	0	0	0			
Comparators	0	0	0	0	0	0	ı	
16-bit timers	0	0	0	0			ı	
LPTIMER	0	0	0	0	0	0		
IWDG	0	0	0	0	0	0	0	0
WWDG	0	0	0	0			1	
SysTick Timer	0	0	0	0			-	
GPIOs	0	0	0	0	0	0		2 pins
Wakeup time to Run mode	0 μs	0.36 µs	3 µs	32 µs		3.5 µs 50 µs		50 µs



#### **Nested vectored interrupt controller (NVIC)**

The ultra-low-power STM32L051x6/8 embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- · provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

### 3.4 Reset and supply management

#### 3.4.1 Power supply schemes

- V<sub>DD</sub> = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V<sub>DD</sub> pins.
- V<sub>SSA</sub>, V<sub>DDA</sub> = 1.65 to 3.6 V: external analog power supplies for ADC reset blocks, RCs and PLL. V<sub>DDA</sub> and V<sub>SSA</sub> must be connected to V<sub>DD</sub> and V<sub>SS</sub>, respectively.

#### 3.4.2 Power supply supervisor

The devices have an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the  $V_{DD}$  threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on  $V_{DD}$  at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the



- 32.768 kHz low-speed external crystal (LSE)
- 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog.
   The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.

#### RTC clock source

The LSI, LSE or HSE sources can be chosen to clock the RTC, whatever the system clock.

#### Startup clock

After reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

#### • Clock security system (CSS)

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled. Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.

## Clock-out capability (MCO: microcontroller clock output)

It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

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#### 3.8 Memories

The STM32L051x6/8 devices have the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 32 or 64 Kbytes of embedded Flash program memory
  - 2 Kbytes of data EEPROM
  - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no protection
- Level 1: memory readout protected.
  - The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- **Level 2**: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (Flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

### 3.9 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- · Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1(PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), USART1(PA9, PA10) or USART2(PA2, PA3). See STM32™ microcontroller system memory boot mode AN2606 for details.

PB7 PB6 PB5 PB4 PB3 32 31 30 29 28 27 26 25 24 PA14 VDD ☐1 PC14-OSC32\_IN 2 23 PA13 PC15-OSC32\_OUT 3 22 PA12 21 PA11 NRST ☐4 LQFP32 20 PA10 VDDA ☐ 5 19 PA9 PA0 🗆 6 18 PA8 17 VDD PA1 ☐ 7 MSv35429V3

Figure 7. STM32L051x6/8 LQFP32 pinout

1. The above figure shows the package top view.

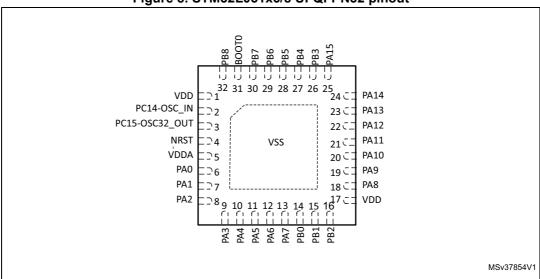


Figure 8. STM32L051x6/8 UFQFPN32 pinout

1. The above figure shows the package top view.

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Table 15. STM32L051x6/8 pin definitions (continued)

		Pin Nu	umber				-			,	
LQFP64	TFBGA64	LQFP48	WLCSP36 <sup>(1)</sup>	LQFP32	UFQFPN32	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
5	C1	5	-	-	-	PH0-OSC_IN (PH0)	I/O	TC	-	-	OSC_IN
6	D1	6	-	-	-	PH1- OSC_OUT (PH1)	I/O	тс	1	-	OSC_OUT
7	E1	7	C6	4	4	NRST	I/O	RST	-	-	-
8	E3	-	-	-	-	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT	ADC_IN10
9	E2	-	-	-	-	PC1	I/O	FT	-	LPTIM1_OUT, EVENTOUT	ADC_IN11
10	F2	-	-	-	-	PC2	I/O	FT	-	LPTIM1_IN2, SPI2_MISO/I2S2_M CK	ADC_IN12
11	-	-	-	ı	-	PC3	I/O	FT	1	LPTIM1_ETR, SPI2_MOSI/I2S2_SD	ADC_IN13
12	F1	8	-	-	-	VSSA	S		-	-	-
-	G1	-	E6	ı	ı	VREF+	S		1	-	-
13	H1	9	D5	5	5	VDDA	S		ı	-	-
14	G2	10	D4	6	6	PA0	I/O	TC	1	TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKU P1
15	H2	11	F6	7	7	PA1	I/O	FT	1	EVENTOUT, TIM2_CH2, USART2_RTS_DE, TIM21_ETR	COMP1_INP, ADC_IN1
16	F3	12	E5	8	8	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, USART2_TX, COMP2_OUT	COMP2_INM6, ADC_IN2
17	G3	13	F5	9	9	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, USART2_RX	COMP2_INP, ADC_IN3
18	C2	-	-	-	-	VSS	S		-	-	-

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>LPBUF</sub> <sup>(4)</sup>	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V <sub>REFINT_DIV1</sub> <sup>(4)</sup>	1/4 reference voltage	-	24	25	26	
V <sub>REFINT_DIV2</sub> <sup>(4)</sup>	1/2 reference voltage	-	49	50	51	% V <sub>REFINT</sub>
V <sub>REFINT_DIV3</sub> <sup>(4)</sup>	3/4 reference voltage	-	74	75	76	IXEI IIVI

Table 26. Embedded internal reference voltage<sup>(1)</sup> (continued)

- Refer to Table 38: Peripheral current consumption in Stop and Standby mode for the value of the internal reference current consumption (I<sub>REFINT</sub>).
- 2. Guaranteed by test in production.
- 3. The internal V<sub>REF</sub> value is individually measured in production and stored in dedicated EEPROM bytes.
- 4. Guaranteed by design.
- 5. Shortest sampling time can be determined in the application by multiple iterations.
- 6. To guarantee less than 1% VREF\_OUT deviation.

#### 6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 13: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code if not specified otherwise

The current consumption values are derived from the tests performed under ambient temperature and V<sub>DD</sub> supply voltage conditions summarized in *Table 23: General operating conditions* unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time and prefetch is adjusted depending on fHCLK frequency and voltage range to provide the best CPU performance unless otherwise specified.
- When the peripherals are enabled f<sub>APB1</sub> = f<sub>APB2</sub> = f<sub>APB</sub>
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used)
- The HSE user clock applied to OSCI\_IN input follows the characteristic specified in Table 40: High-speed external user clock characteristics
- For maximum current consumption V<sub>DD</sub> = V<sub>DDA</sub> = 3.6 V is applied to all supply pins
- For typical current consumption V<sub>DD</sub> = V<sub>DDA</sub> = 3.0 V is applied to all supply pins if not specified otherwise

The parameters given in *Table 47*, *Table 23* and *Table 24* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 23*.



#### On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- $\bullet$   $\,$  all I/O pins are in input mode with a static value at  $V_{DD}$  or  $V_{SS}$  (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked OFF
  - with only one peripheral clocked on

Table 37. Peripheral current consumption in Run or Sleep mode<sup>(1)</sup>

Peripheral		Typical	consumption, V	/ <sub>DD</sub> = 3.0 V, T <sub>A</sub> =	25 °C	
		Range 1, V <sub>CORE</sub> =1.8 V VOS[1:0] = 01	Range 2, V <sub>CORE</sub> =1.5 V VOS[1:0] = 10	Range 3, V <sub>CORE</sub> =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit
	I2C1	11	9.5	7.5	9	
	I2C2	4	3.5	3	2.5	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	
APB1	SPI2	9	4.5	3.5	4	μΑ/MHz (f <sub>HCLK</sub> )
	USART2	14.5	12	9.5	11	('HCLK)
	TIM2	10.5	8.5	7	9	
	TIM6	3.5	3	2.5	2	
	WWDG	3	2	2	2	
	ADC1 <sup>(2)</sup>	5.5	5	3.5	4	
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
APB2	TIM21	7.5	6	5	5.5	μΑ/MHz
APB2	TIM22	7	6	5	6	(f <sub>HCLK</sub> )
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	
	GPIOA	3.5	3	2.5	2.5	
Cortex-	GPIOB	3.5	2.5	2	2.5	μΑ/MHz
M0+ core I/O port	GPIOC	8.5	6.5	5.5	7	(f <sub>HCLK</sub> )
	GPIOD	1	0.5	0.5	0.5	
	CRC	1.5	1	1	1	
AHB	FLASH	0(3)	0(3)	0(3)	0 <sup>(3)</sup>	μΑ/MHz (f <sub>HCLK</sub> )
	DMA1	10	8	6.5	8.5	('HCLK)



#### 6.3.6 **External clock source characteristics**

### High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in Section 6.3.12. However, the recommended clock input waveform is shown in Figure 19.

Table 40. High-speed external user clock characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	User external clock source	CSS is ON or PLL is used	1	8	32	MHz
f <sub>HSE_ext</sub>	frequency	CSS is OFF, PLL not used	0	8	32	MHz
V <sub>HSEH</sub>	OSC_IN input pin high level voltage		0.7V <sub>DD</sub>	-	$V_{DD}$	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage		V <sub>SS</sub>	ı	0.3V <sub>DD</sub>	V
$t_{w(HSE)} \ t_{w(HSE)}$	OSC_IN high or low time		12	ı	-	ns
t <sub>r(HSE)</sub>	OSC_IN rise or fall time	-	-	-	20	113
C <sub>in(HSE)</sub>	OSC_IN input capacitance		-	2.6	-	pF
DuCy <sub>(HSE)</sub>	Duty cycle		45	ı	55	%
ΙL	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	ı	±1	μΑ

<sup>1.</sup> Guaranteed by design.

 $V_{\mathsf{HSEH}}$ 90% 10%  $V_{HSEL}$ -T<sub>HSE</sub>  $f_{\mathsf{HSE\_ext}}$ EXTERNAL CLOCK SOURCE OSC\_IN STM32Lxx ai18232c

Figure 19. High-speed external clock source AC timing diagram

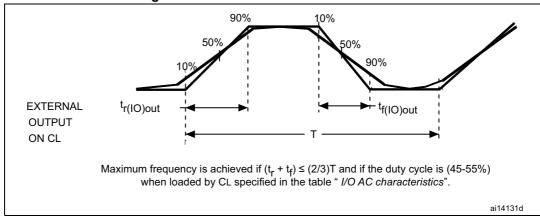


Figure 26. I/O AC characteristics definition

### 6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R<sub>PU</sub>, except when it is internally driven low (see *Table 59*).

Unless otherwise specified, the parameters given in *Table 59* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 23*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST input low level voltage	-	$V_{SS}$	-	8.0	
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST input high level voltage	-	1.4	-	$V_{DD}$	
V(1)	NRST output low level	I <sub>OL</sub> = 2 mA 2.7 V < V <sub>DD</sub> < 3.6 V	-	-	0.4	٧
V <sub>OL(NRST)</sub> <sup>(1)</sup>	voltage	I <sub>OL</sub> = 1.5 mA 1.65 V < V <sub>DD</sub> < 2.7 V	-	-	0.4	
V <sub>hys(NRST)</sub> <sup>(1)</sup>	NRST Schmitt trigger voltage hysteresis	-	ı	10%V <sub>DD</sub> <sup>(2)</sup>	ı	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(3)</sup>	$V_{IN} = V_{SS}$	30	45	60	kΩ
V <sub>F(NRST)</sub> <sup>(1)</sup>	NRST input filtered pulse	-	1	-	50	ns
V <sub>NF(NRST)</sub> <sup>(1)</sup>	NRST input not filtered pulse	-	350	-	-	ns

Table 59. NRST pin characteristics

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<sup>1.</sup> Guaranteed by design.

<sup>2. 200</sup> mV minimum value

The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

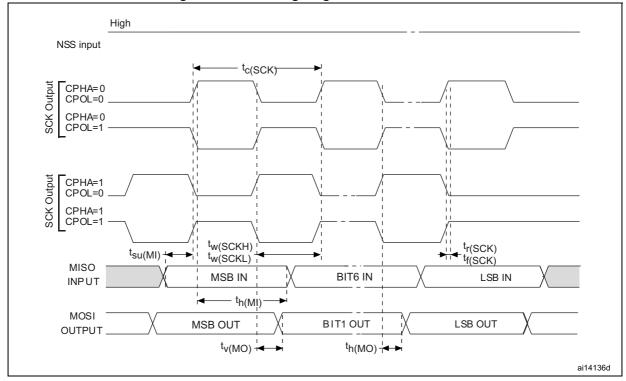


Figure 34. SPI timing diagram - master mode<sup>(1)</sup>

1. Measurement points are done at CMOS levels:  $0.3V_{DD}$  and  $0.7V_{DD}$ .



Table 75. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data (continued)

Symbol		millimeters			inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 41. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball ,grid array recommended footprint

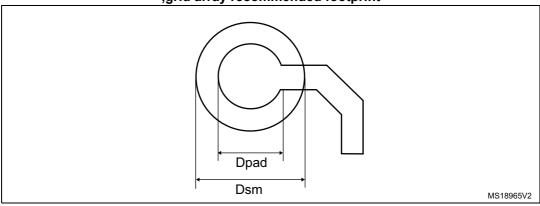


Table 76. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.27 mm
Dsm	0.35 mm typ. (depends on the soldermask registration tolerance)
Solder paste	0.27 mm aperture diameter.

Note: Non solder mask defined (NSMD) pads are recommended.

4 to 6 mils solder paste screen printing process.



#### **Device marking for LQFP48**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

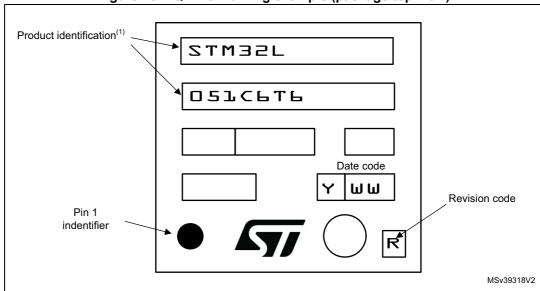


Figure 45. LQFP48 marking example (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



Table 78. Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale mechanical data (continued)

Symbol	millimeters				inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max
F	-	0.305 <sup>(3)</sup>	-	-	0.012	-
G	-	0.440 <sup>(3)</sup>	-	-	0.017	-
aaa	-	-	0.100	-	-	0.004
bbb	-	-	0.100	-	-	0.004
ccc	-	-	0.100	-	-	0.004
ddd	-	-	0.050	-	-	0.002
eee	-	-	0.050	-	-	0.002

- 1. Values in inches are converted from mm and rounded to the 3rd decimal place.
- 2. Nominal dimension rounded to the 3rd decimal place results from process capability.
- 3. Calculated dimensions are rounded to the 3rd decimal place.

Figure 47. Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale recommended footprint

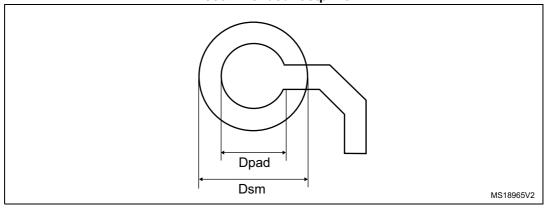


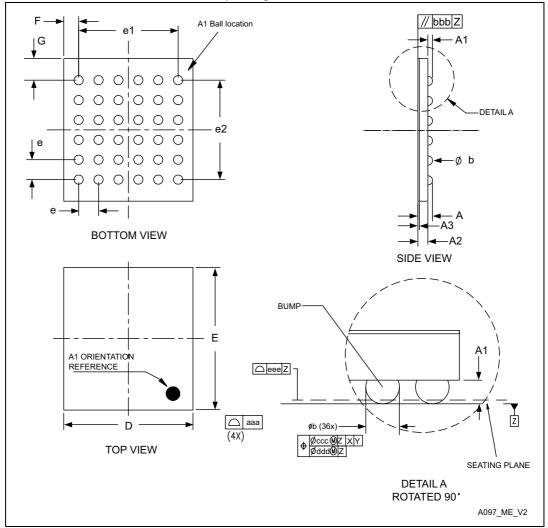
Table 79. Standard WLCSP36 recommended PCB design rules

Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 μm min. (for 260 μm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed



## 7.5 Thin WLCSP36 package information

Figure 49. Thin WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale package outline



- 1. Drawing is not to scale.
- 2. b dimensions is measured at the maximum bump diameter parallel to primary datum Z.
- 3. Primary datum Z and seating plane are defined by the spherical crowns of the bump.
- 4. Bump position designation per JESD 95-1, SPP-010.

#### **Device marking for LQFP32**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

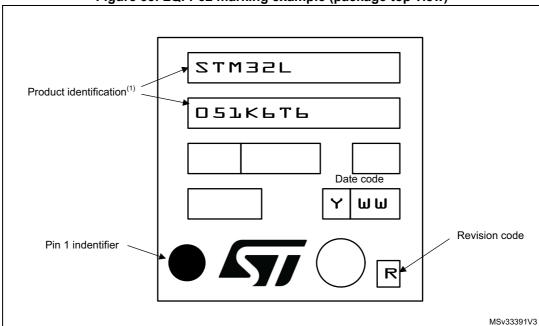


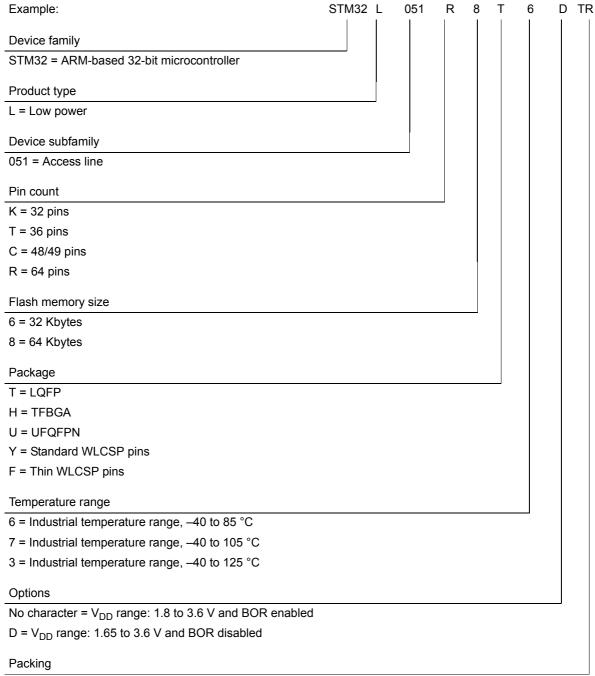
Figure 53. LQFP32 marking example (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



## 8 Part numbering

Table 85. STM32L051x6/8 ordering information scheme



TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

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Table 86. Document revision history (continued)

Date	Revision	Changes
<b>Date</b> 07-Mar-2017	Revision 7	Changes  Added thin WLCSP36 package  Updated number of I2S interfaces in Table 2: Ultra-low-power STM32L051x6/x8 device features and peripheral counts.  Removed note 2 related to PA4 in Table 15: STM32L051x6/8 pin definitions  Added mission profile compliance with JEDEC JESD47 in Section 6.2: Absolute maximum ratings.  Removed CRS from Table 37: Peripheral current consumption in Run or Sleep mode.  Added note 2. related to the position of the external capacitor below Figure 27: Recommended NRST pin protection.  Updated R <sub>L</sub> in Table 60: ADC characteristics.  Updated t <sub>AF</sub> maximum value for range 1 in Table 68: I2C analog filter characteristics.  Updated t <sub>WUUSART</sub> description in Table 69: USART/LPUART characteristics.
		. , , , , , , , , , , , , , , , , , , ,
		Added reference to optional marking or inset/upset marks in all package device marking sections.
		Previous WLCSP36 package renamed "Standard" WLCSP36; added Note 2. below Figure 46: Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale package outline and updated Table 78: Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale mechanical data.

